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Electrical contacts to two-dimensional semiconductors

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1143	Ultrahigh Conductivity in Two-Dimensional InSe via Remote Doping at Room Temperature.		
1142	High-Performance InSe Transistors with Ohmic Contact Enabled by Nonrectifying Barrier-Type Indium Electrodes.		
1141	Optical Control of Spin Polarization in Monolayer Transition Metal Dichalcogenides.		
1140	Inducing Strong Superconductivity in WTe ₂ by a Proximity Effect.		
1139	Low-Temperature Ohmic Contact to Monolayer MoS ₂ by van der Waals Bonded Co/hBN Electrodes.		
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